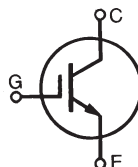


GenX3™ 1200V IGBTs

IXGK82N120B3 IXGX82N120B3

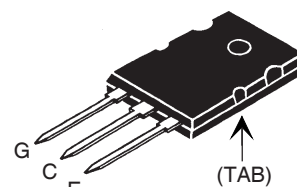
$$\begin{aligned} V_{CES} &= 1200V \\ I_{C110} &= 82A \\ V_{CE(sat)} &\leq 3.20V \end{aligned}$$

High-Speed Low-Vsat PT IGBTs
for 3 - 20 kHz Switching

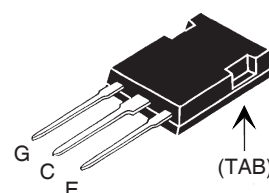


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GE} = 1M\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Chip Capability)	230	A
I_{C110}	$T_C = 110^\circ\text{C}$	82	A
I_{LRMS}	$T_C = 25^\circ\text{C}$ (Lead RMS Limit)	120	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	500	A
I_A	$T_C = 25^\circ\text{C}$	41	A
E_{AS}	$T_C = 25^\circ\text{C}$	750	mJ
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 2\Omega$ Clamped Inductive Load	$I_{CM} = 164$ $V_{CE} \leq V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	1250	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	$^\circ\text{C}$
M_d	Mounting Torque (IXGK)	1.13/10	Nm/lb.in.
F_C	Mounting Force (IXGX)	20..120/4.5..14.6	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXGK)



PLUS247™ (IXGX)



G = Gate E = Emitter
C = Collector TAB = Collector

Features

- Optimized for Low Conduction and Switching Losses
- Square RBSOA
- High Avalanche Capability
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- SMPS
- PFC Circuits
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}$, $V_{CE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 1mA$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ\text{C}$, Note 1			50 μA 5 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = I_{C110}$, $V_{GE} = 15V$, Note 2 $T_J = 125^\circ\text{C}$		2.70 2.64	3.20 V V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}$, $V_{CE} = 10\text{V}$, Note 2	35	60	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		7900	pF
C_{oes}			640	pF
C_{res}			170	pF
$Q_{g(on)}$	$I_C = I_{C110}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		350	nC
Q_{ge}			50	nC
Q_{gc}			150	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 80\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}$, $R_G = 2\Omega$ Note 3		30	ns
t_{ri}			77	ns
E_{on}			5.0	mJ
$t_{d(off)}$			210	ns
t_{fi}			100	ns
E_{off}			3.3	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 80\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}$, $R_G = 2\Omega$ Note 3		32	ns
t_{ri}			80	ns
E_{on}			6.8	mJ
$t_{d(off)}$			240	ns
t_{fi}			520	ns
E_{off}			7.1	mJ
R_{thJC}				0.10 $^\circ\text{C/W}$
R_{thCK}			0.15	$^\circ\text{C/W}$

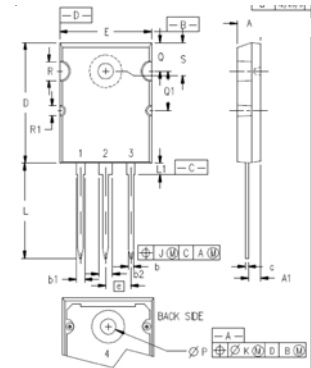
Notes:

1. Part must be heatsunk for high-temp I_{ces} measurement.
2. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.
3. Switching times & energy losses may increase for higher $V_{CE}(\text{Clamp})$, T_J or R_G .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

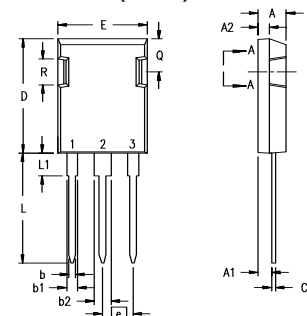
TO-264 (IXGK) Outline



1 - GATE
2, 4 - DRAIN (COLLECTOR)
3 - SOURCE (EMITTER)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b1	.037	.055	0.94	1.40
b2	.087	.102	2.21	2.59
c	.110	.126	2.79	3.20
D	.017	.029	0.43	0.74
E	1.007	1.047	25.58	26.59
L	.760	.799	19.30	20.29
L1	.215 BSC		5.46 BSC	
Q	.000	.010	0.00	0.25
Q1	.000	.010	0.00	0.25
R	.779	.842	19.79	21.39
R1	.087	.102	2.21	2.59
S	.122	.138	3.10	3.51
T	.240	.256	6.10	6.50
U	.330	.346	8.38	8.79
V	.155	.187	3.94	4.75
W	.085	.093	2.16	2.36
X	.243	.253	6.17	6.43

PLUS247™ (IXGX) Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b1	1.14	1.40	.045	.055
b2	1.91	2.13	.075	.084
c	2.92	3.12	.115	.123
D	0.61	0.80	.024	.031
E	20.80	21.34	.819	.840
L	15.75	16.13	.620	.635
L1	5.45 BSC		.215 BSC	
Q	19.81	20.32	.780	.800
Q1	3.81	4.32	.150	.170
R	5.59	6.20	.220	0.244
S	4.32	4.83	.170	.190

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics
@ 25°C

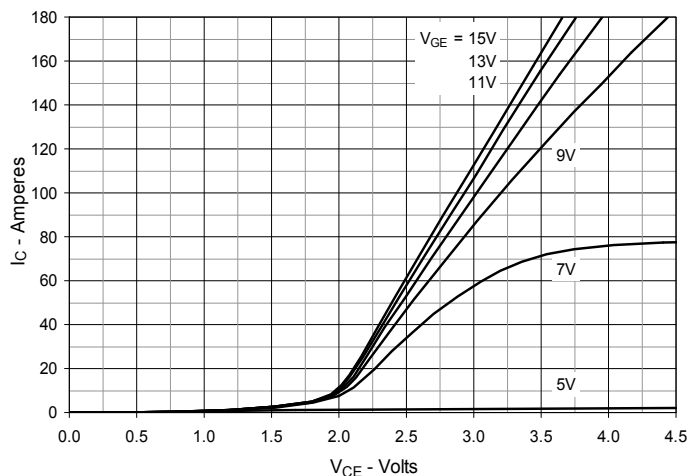


Fig. 2. Extended Output Characteristics
@ 25°C

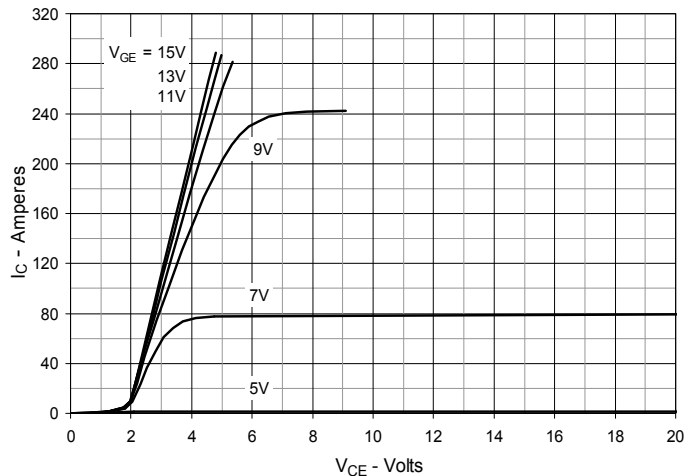


Fig. 3. Output Characteristics
@ 125°C

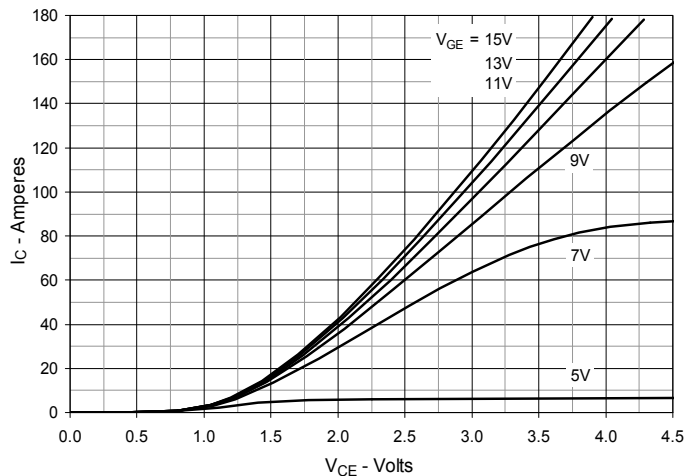


Fig. 4. Dependence of $V_{CE(sat)}$ on
Junction Temperature

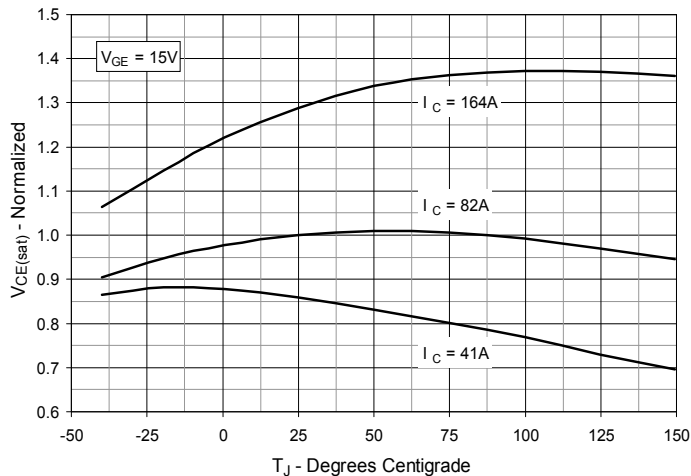


Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter Voltage

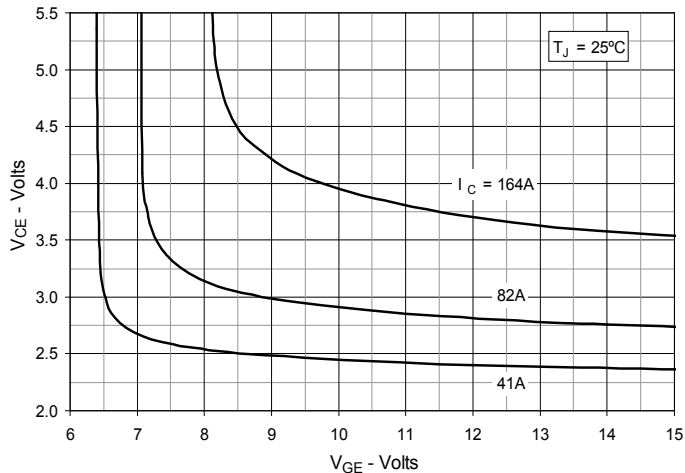


Fig. 6. Input Admittance

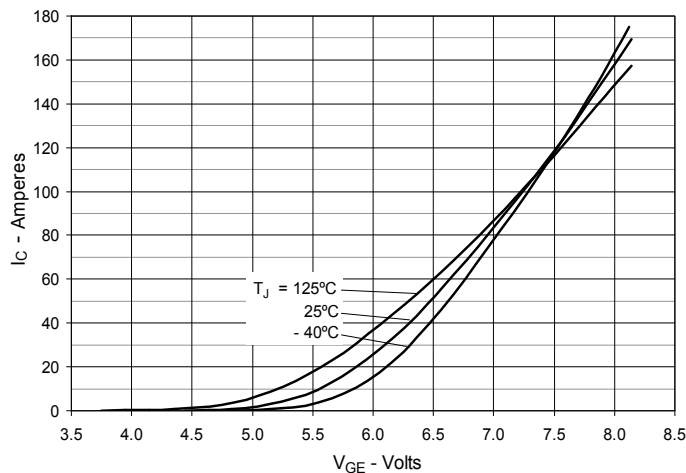


Fig. 7. Transconductance

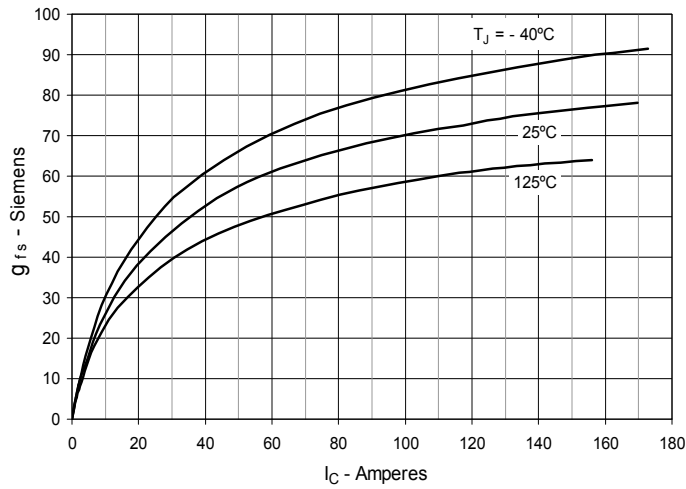


Fig. 8. Gate Charge

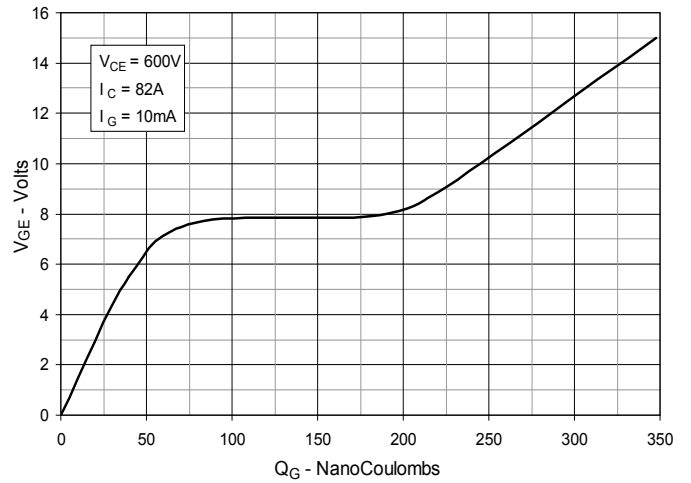


Fig. 9. Capacitance

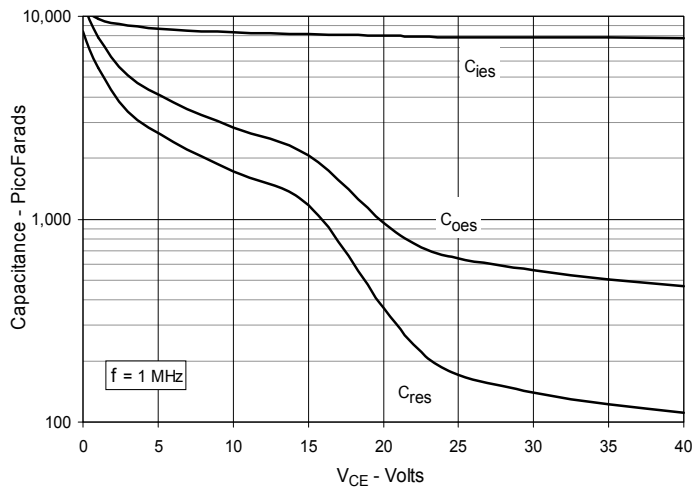


Fig. 10. Reverse-Bias Safe Operating Area

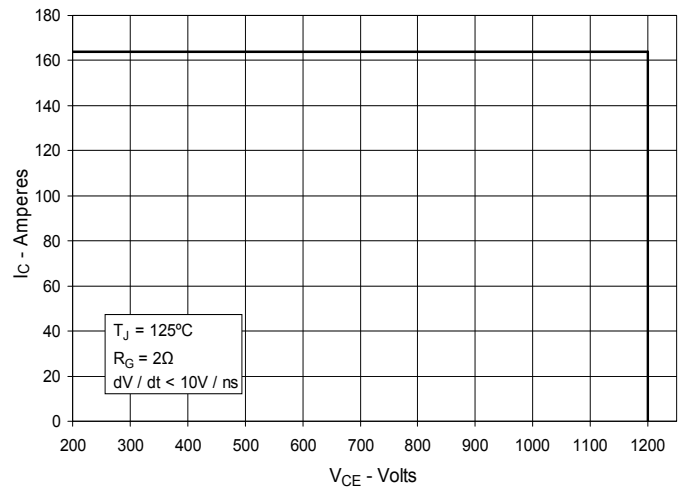
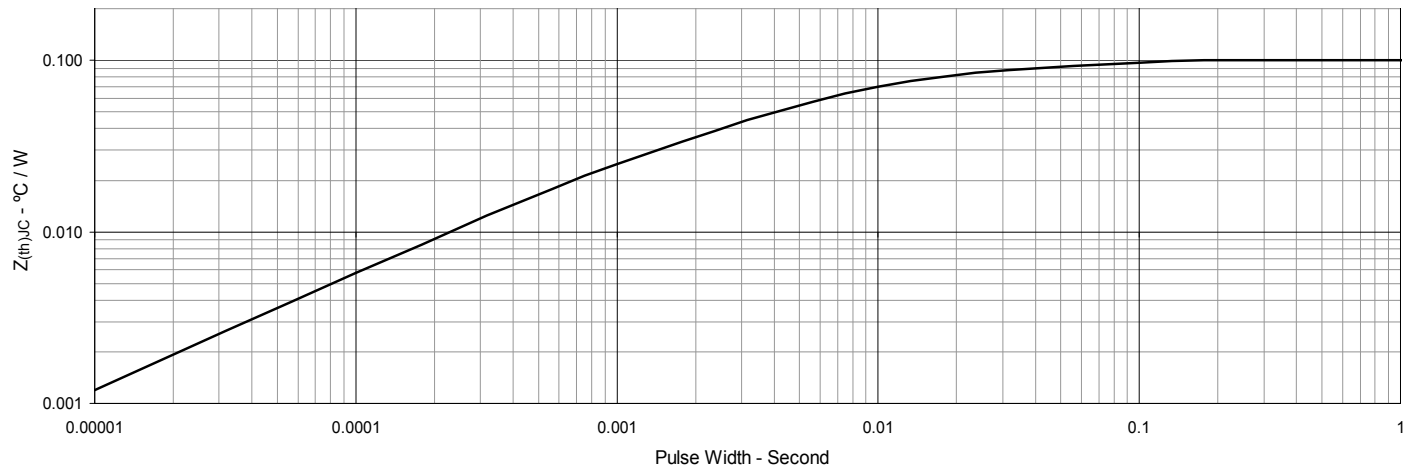
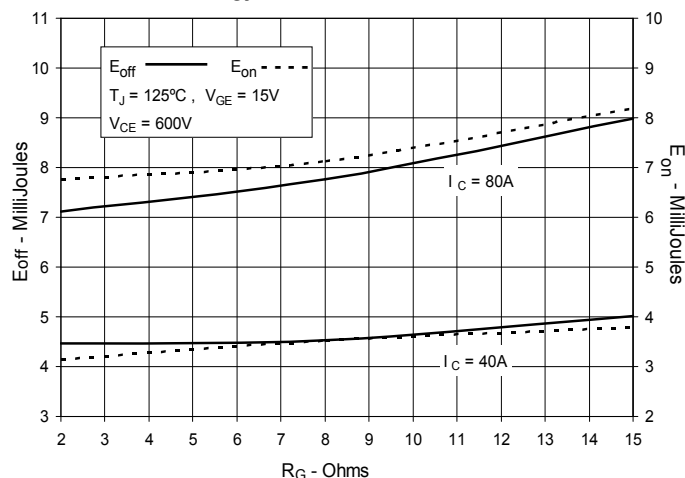


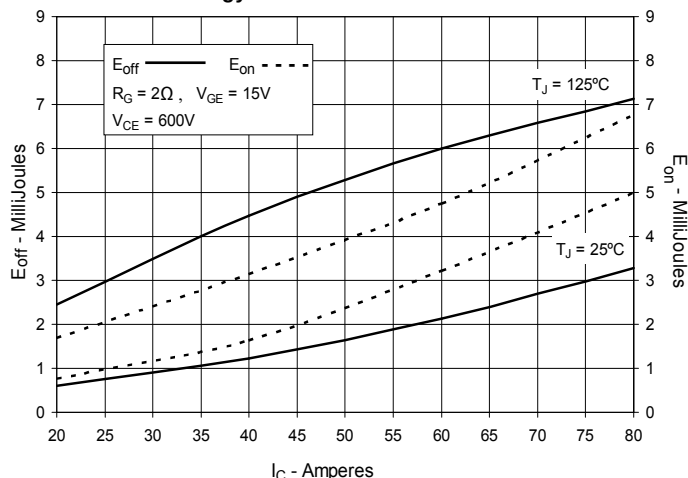
Fig. 11. Maximum Transient Thermal Impedance



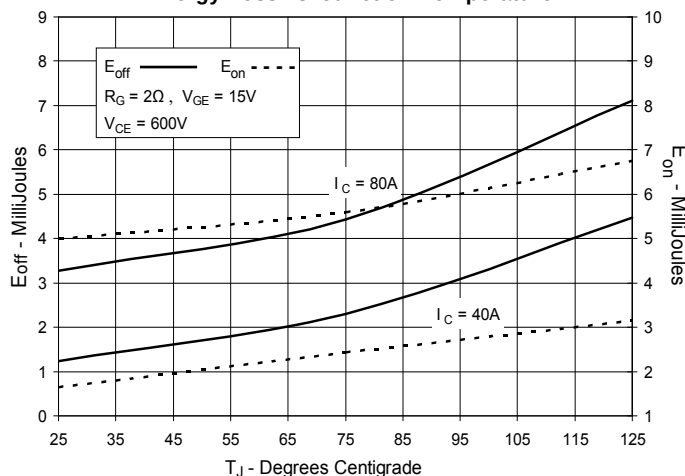
**Fig. 12. Inductive Switching
Energy Loss vs. Gate Resistance**



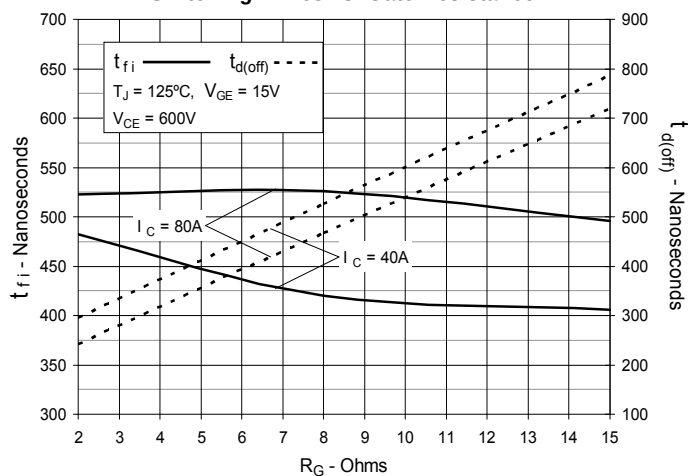
**Fig. 13. Inductive Switching
Energy Loss vs. Collector Current**



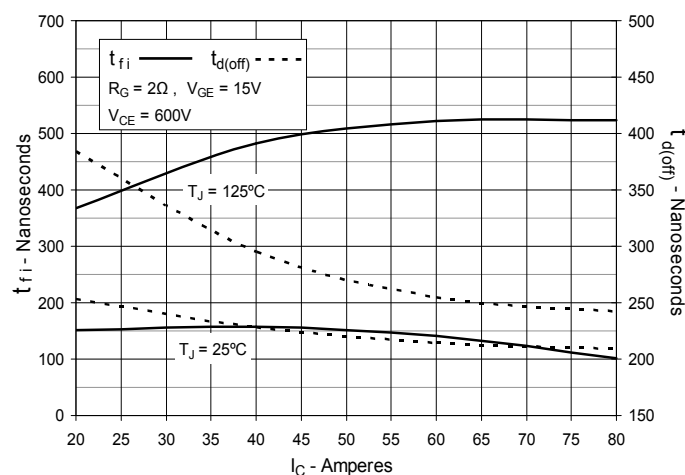
**Fig. 14. Inductive Switching
Energy Loss vs. Junction Temperature**



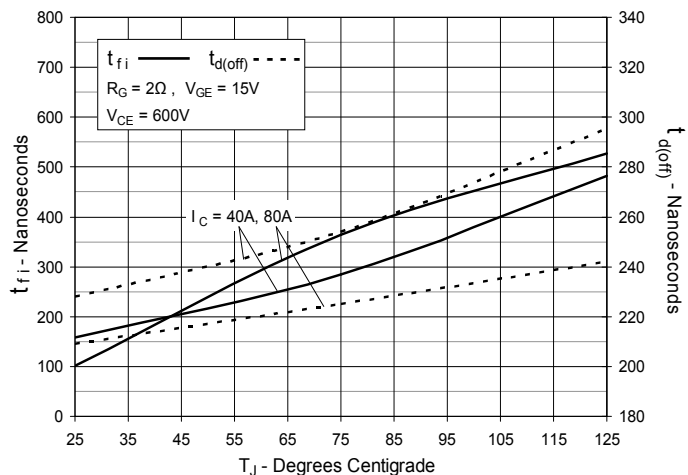
**Fig. 15. Inductive Turn-off
Switching Times vs. Gate Resistance**



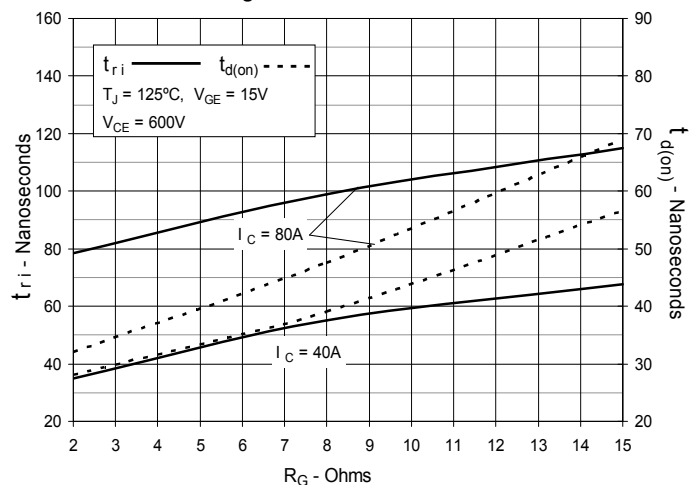
**Fig. 16. Inductive Turn-off
Switching Times vs. Collector Current**



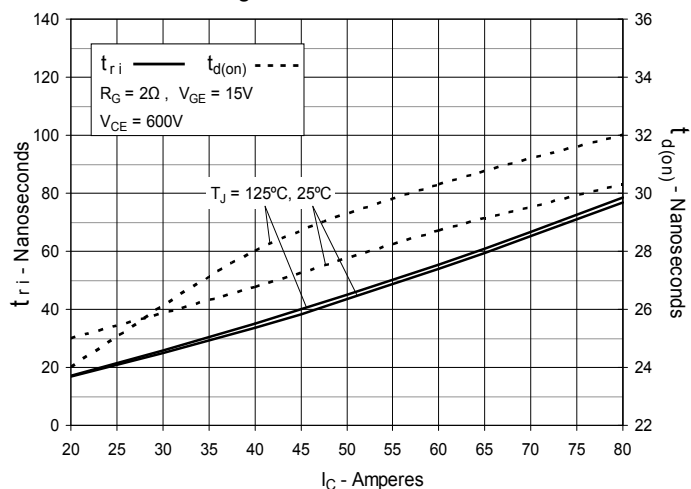
**Fig. 17. Inductive Turn-off
Switching Times vs. Junction Temperature**



**Fig. 18. Inductive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on
Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on
Switching Times vs. Junction Temperature**

